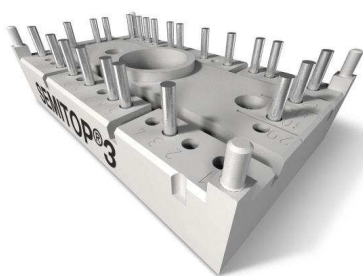


SK10DGDL12T4ET



SEMITOP®3

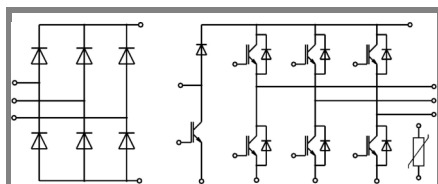
**3-phase bridge rectifier +
brake chopper + 3-phase
bridge inverter**
SK 10 DGDL 12T4 ET

Target Data

Features

- One screw mounting module
- Trench4 IGBT technology
- CAL4 technology FWD
- Integrated NTC temperature sensor

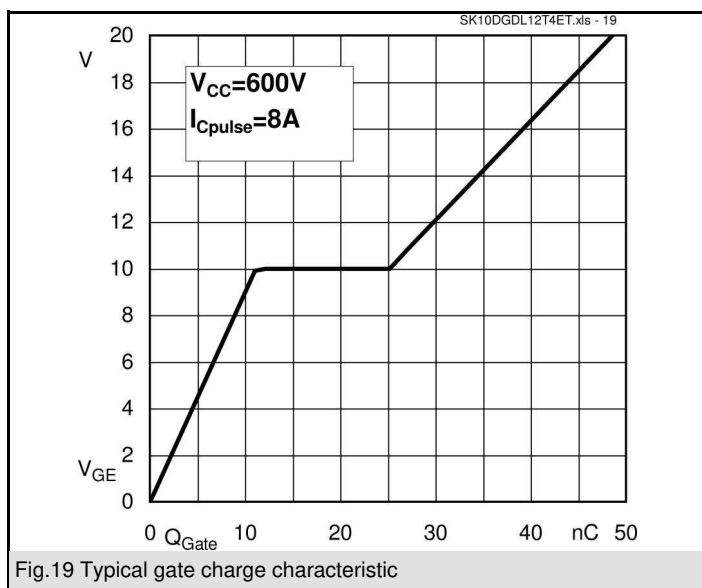
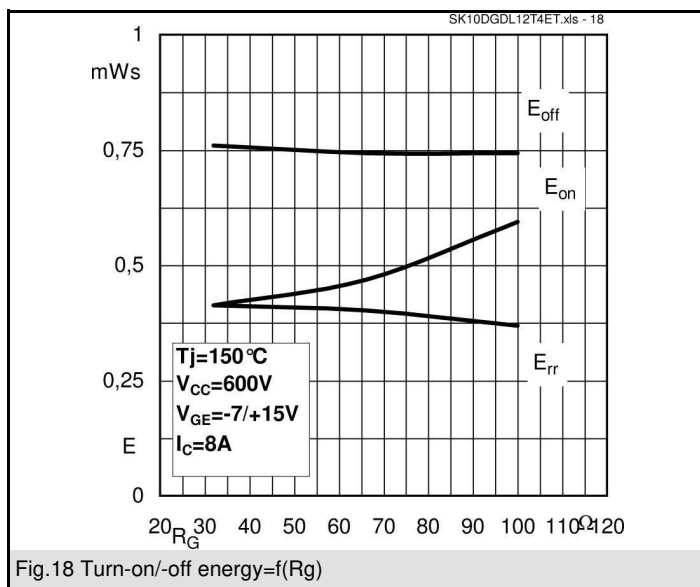
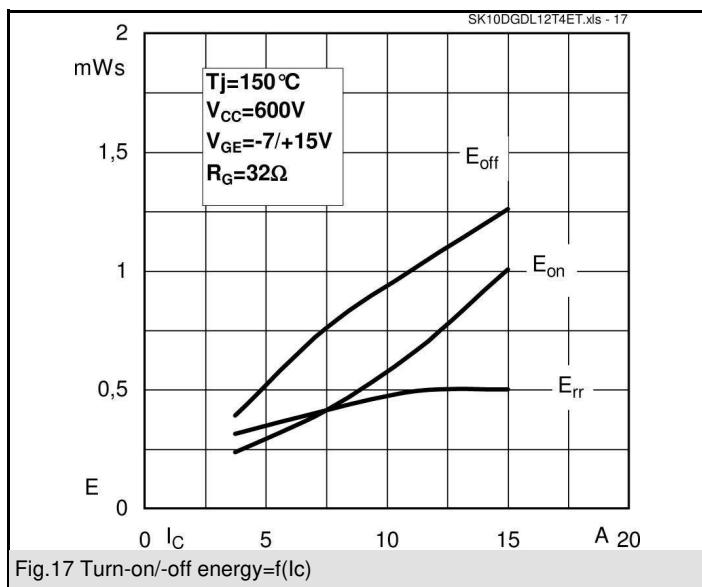
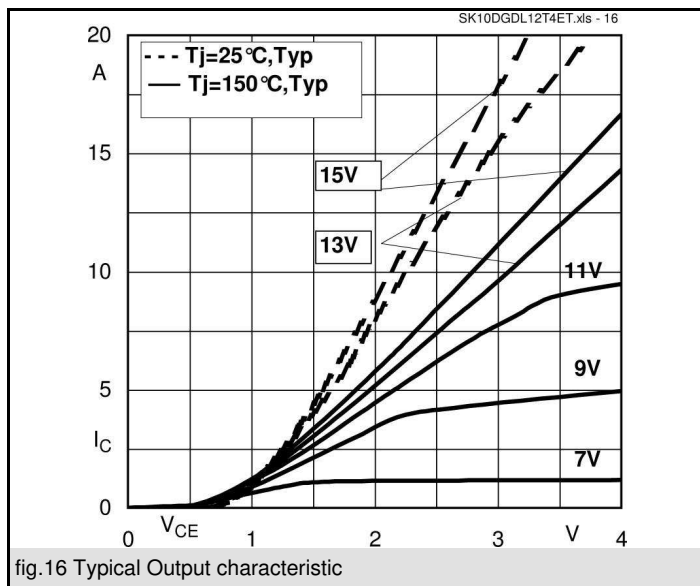
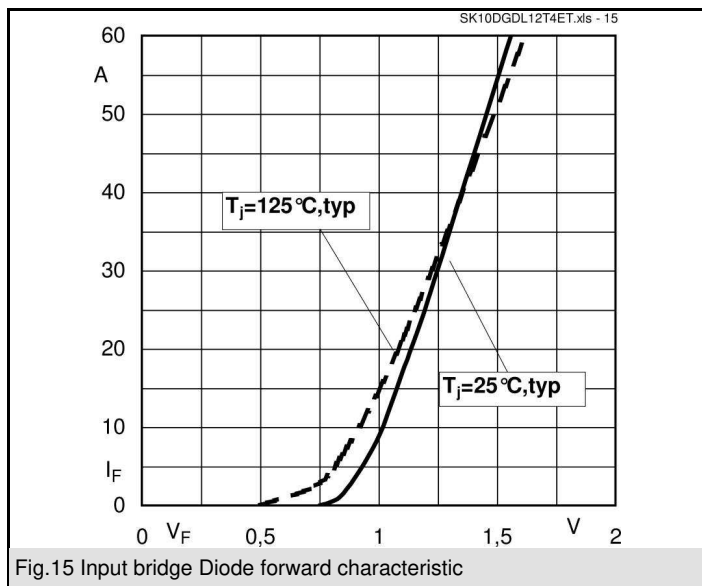
1) $V_{CE,sat}$, V_F = chip level value

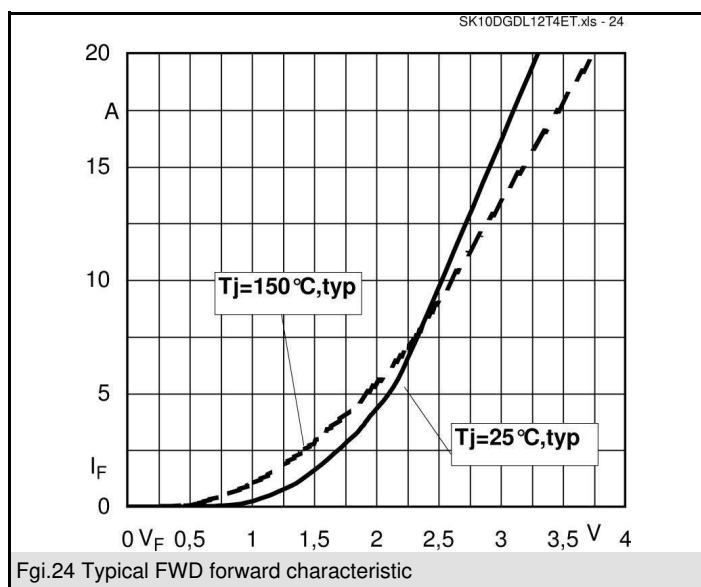
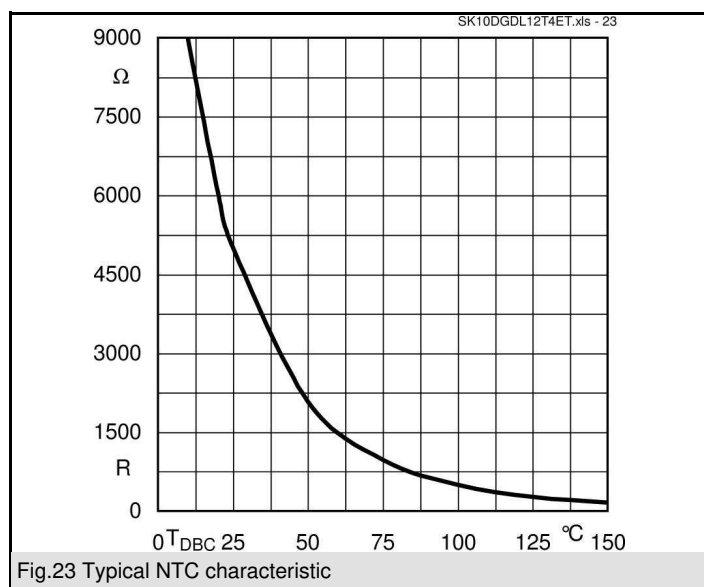
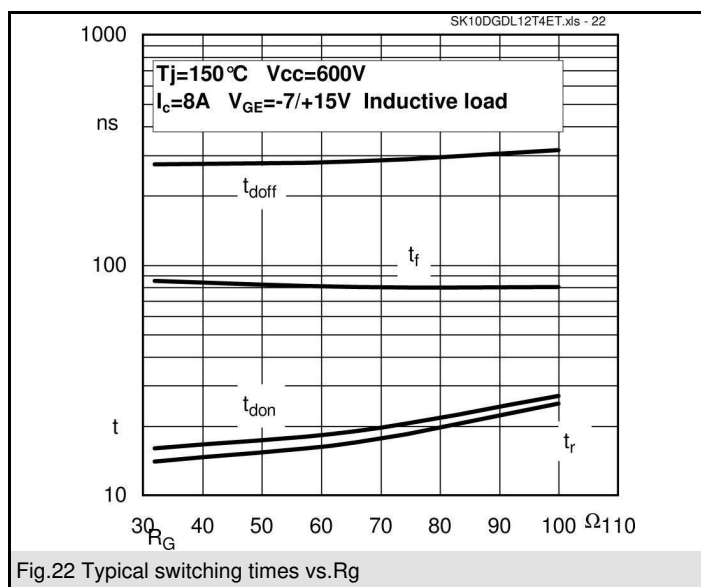
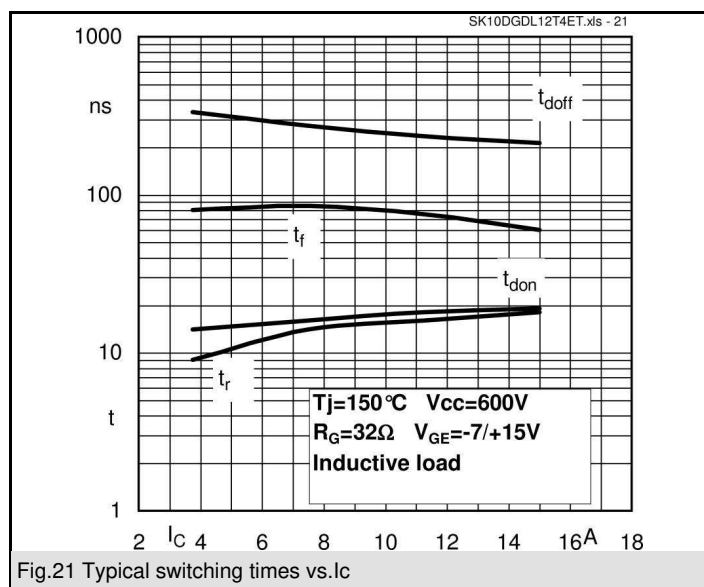


DGDL - ET

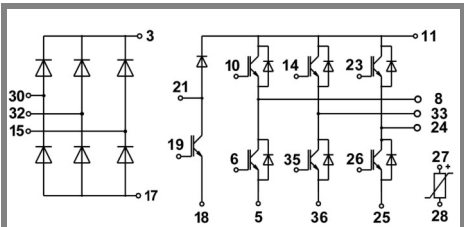
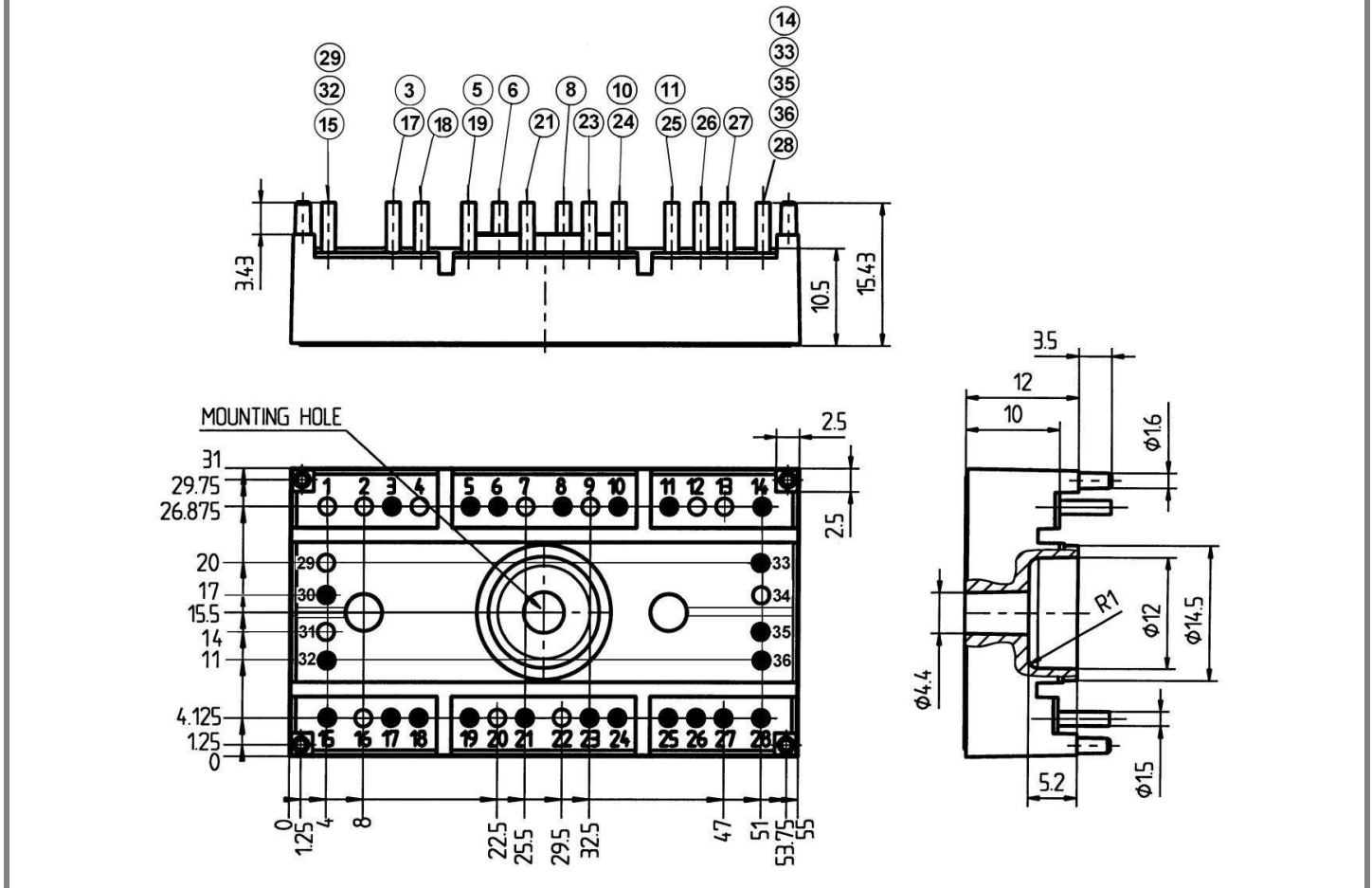
Absolute Maximum Ratings		Ts = 25 °C, unless otherwise specified	
Symbol	Conditions	Values	Units
IGBT - Inverter,Chopper			
V_{CES}	$T_s = 25 (70) ^\circ C$	1200	V
I_C	$I_{CRM} = 3 \times I_{Cnom}$, $t_p = 1 \text{ ms}$	17 (15)	A
I_{CRM}		24	A
V_{GES}		± 20	V
T_j		-40 ... +175	$^\circ C$
Diode - Inverter,Chopper			
I_F	$T_s = 25 (70) ^\circ C$	15 (12)	A
I_{FRM}	$I_{FRM} = 2 \times I_{Fnom}$, $t_p = 1 \text{ ms}$	24	A
T_j		-40 ... +150	$^\circ C$
Rectifier			
V_{RRM}	$T_s = 70 ^\circ C$	1600	V
I_F	$t_p = 10 \text{ ms}$, $\sin 180 ^\circ$, $T_j = 25 ^\circ C$	28	A
I_{FSM} / I_{TSM}	$t_p = 10 \text{ ms}$, $\sin 180 ^\circ$, $T_j = 25 ^\circ C$	220	A
I_t^2		240	A ² s
T_j		-40 ... +175	$^\circ C$
T_{sol}	Terminals, 10 s	260	$^\circ C$
T_{stg}		-40 ... +125	$^\circ C$
V_{isol}	AC, 1 min. / 1 s	2500 / 3000	V

Characteristics		Ts = 25 °C, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT - Inverter					
V _{CEsat}	I _C = 8 A, T _j = 25 (150) °C	5	1,85 (2,25)	2,05 (2,45)	V
V _{GE(th)}	V _{GE} = V _{CE} , I _C = 0,3 mA		5,8	6,5	V
V _{CE(TO)}	T _j = 25 °C (150) °C		1,1 (1)	1,3 (1,2)	V
r _T	T _j = 25 °C (150) °C		93,8 (156)		mΩ
C _{ies}	V _{CE} = 25 V, V _{GE} = 0 V, f = 1 MHz		0,49		nF
C _{oes}	V _{CE} = 25 V, V _{GE} = 0 V, f = 1 MHz		0,05		nF
C _{res}	V _{CE} = 25 V, V _{GE} = 0 V, f = 1 MHz		0,03		nF
R _{th(j-s)}	per IGBT		2,2		K/W
t _{d(on)}	under following conditions		16		ns
t _r	V _{CC} = 600 V, V _{GE} = ± 15 V		14		ns
t _{d(off)}	I _C = 8 A, T _j = 150 °C		273		ns
t _f	R _{Gon} = R _{Goff} = 32 Ω		85		ns
E _{on}	inductive load		0,41		mJ
E _{off}			0,75		mJ
Diode - Inverter,Chopper					
V _F = V _{EC}	I _F = 15 A, T _j = 25(150) °C		2,38 (2,44)	2,71 (2,77)	V
V _(TO)	T _j = 25 °C (150) °C		1,3 (0,9)	1,5 (1,1)	V
r _T	T _j = 25 °C (150) °C		135 (192)	151,3 (208,8)	mΩ
R _{th(j-s)}	per diode		2,7		K/W
I _{RRM}	under following conditions		15		A
Q _{rr}	I _F = 8 A, V _R = 600 V		0,2		μC
E _{rr}	V _{GE} = 0 V, T _j = 150 °C		0,41		mJ
	di _F /dt = 1375 A/μs				
Diode - Rectifier					
V _F	I _F = 15 A, T _j = 25() °C		1,1		V
V _(TO)	T _j = 150 °C		0,9		V
r _T	T _j = 150 °C		20		mΩ
R _{th(j-s)}	per diode		2		K/W
Temperatur sensor					
R _{ts}	5 %, T _r = 25 (100) °C		5000(493)		Ω
Mechanical data					
w			30		g
M _s	Mounting torque	2,25		2,5	Nm





Dimensions in mm



Case T 49

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.